

	Hits	Search Text	DBs
1	600	thin adj film with (pattern\$3 etch\$3) with (ion adj beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	617	thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	17	((thin adj film near2 (pattern\$3 etch\$3) near2 ((ion cluster focused) near beam)) with (strip strippable ash\$3 photoresist mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	19	((thin adj film near2 (pattern\$3 etch\$3) near2 ((ion cluster focused) near beam)) same (strip strippable ash\$3 photoresist mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	75	thin adj film near2 (pattern\$3 etch\$3) near2 ((ion cluster focused) near beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	185	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) same (strip strippable ash\$3 photoresist mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	151	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) with (strip strippable ash\$3 photoresist mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	2	((thin adj film near2 (pattern\$3 etch\$3) near2 ((ion cluster focused) near beam)) and (ION IONIC CLUSTER CHARGED PARTICLE) NEAR BEAM near (etch\$3 pattern\$3) near (strippable photoresist resist mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	23	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) same (strip strippable ash\$3 photoresist mask)) and (ION IONIC CLUSTER CHARGED PARTICLE) NEAR BEAM near (etch\$3 pattern\$3) near (strippable photoresist resist mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	26	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and (ION IONIC CLUSTER CHARGED PARTICLE) NEAR BEAM near (etch\$3 pattern\$3) near (strippable photoresist resist mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	3	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and (ION IONIC CLUSTER CHARGED PARTICLE) NEAR BEAM near (etch\$3 pattern\$3) near (strippable photoresist resist mask)) not (((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) same (strip strippable ash\$3 photoresist mask)) and (ION IONIC CLUSTER CHARGED PARTICLE) NEAR BEAM near (etch\$3 pattern\$3) near (strippable photoresist resist mask))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	15	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and ((etch\$3 pattern\$3) near (resist photoresist) near ((ION IONIC CLUSTER focused CHARGED PARTICLE) NEAR BEAM))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	58	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and lift adj off	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	27	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and lift adj off) and magnet\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	24	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and lift adj off) and magnet\$2 with thin adj film	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	5	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and lift adj off) and magnet\$2 near thin adj film	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	69	thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) and (liftoff lift-off lift adj off)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	16	thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) same (liftoff lift-off lift adj off)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
19	53	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) and (liftoff lift-off lift adj off)) not (thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) same (liftoff lift-off lift adj off)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	3241	focused adj ion adj beam	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	0	((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) and (liftoff lift-off lift adj off)) not (thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) same (liftoff lift-off lift adj off))) and (focused adj ion adj beam with pattern\$3 with (mask resist photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	180	focused adj ion adj beam with pattern\$3 with (mask resist photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	2	focused adj ion adj beam adj lithography with pattern\$3 with (mask resist photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	42	focused adj ion adj beam adj lithography	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	9	(US-4405710-\$ or US-5236547-\$ or US-5399546-\$ or US-5446016-\$ or US-5506197-\$ or US-5793579-\$ or US-6245249-\$ or US-6391216-\$ or US-6407547-\$).did.	USPAT
26	4306	etch\$3 same ground\$3 with (film layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
27	361	etch\$3 with ground\$3 near (film layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
28	51	etch\$3 near ground\$3 near (film layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
29	44	etch\$3 adj ground\$3 near (film layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
30	36	etch\$3 adj ground\$3 adj (film layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
31	2	(etch\$3 adj ground\$3 adj (film layer)) and (ion adj beam FIB RIBe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
32	2	(etch\$3 adj ground\$3 near (film layer)) and (ion adj beam FIB RIBe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
33	20	(etch\$3 with ground\$3 near (film layer)) and (ion adj beam FIB RIBe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
34	172	(etch\$3 same ground\$3 with (film layer)) and (ion adj beam FIB RIBe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
35	3	(etch\$3 near ground\$3 near (film layer)) and (ion adj beam FIB RIBe)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
36	17	((etch\$3 with ground\$3 near (film layer)) and (ion adj beam FIB RIBe)) not ((etch\$3 near ground\$3 near (film layer)) and (ion adj beam FIB RIBe))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
37	22	(etch\$3 same ground\$3 with (film layer)) and (focused adj ion adj beam FIB)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB